Preliminary Information

DIM750ASM65-TL000

Single Switch IGBT Module

Replaces DS6294-1

DS6294-2 June 2019 (LN38938)

FEATURES

- 10µs Short Circuit Withstand
- High Thermal Cycling Capability
- Soft Punch Through Silicon
- Isolated AlSiC Base with AlN Substrates
- Lead Free construction

APPLICATIONS

- High Reliability Inverters
- Motor Controllers
- Traction Drives
- Choppers

The Powerline range of high power modules includes half bridge, chopper, dual, single and bi-directional switch configurations covering voltages from 600V to 6500V and currents up to 2400A.

The DIM750ASM65-TL000 is a single switch 6500V, soft punch through n-channel enhancement mode, insulated gate bipolar transistor (IGBT) module. The IGBT has a wide reverse bias safe operating area (RBSOA) plus 10µs short circuit withstand. This device is optimised for traction drives and other applications requiring high thermal cycling capability.

The module incorporates an electrically isolated base plate and low inductance construction enabling circuit designers to optimise circuit layouts and utilise grounded heat sinks for safety.

ORDERING INFORMATION

Order As:

DIM750ASM65-TL000

Note: When ordering, please use the complete part number

KEY PARAMETERS

V_{CES}		**6500V**
$V_{CE(sat)}$ *	**(typ)**	**2.5V**
I_C	**(max)**	**750A**
$I_{C(PK)}$	**(max)**	**1500A**

* Measured at the auxiliary terminals

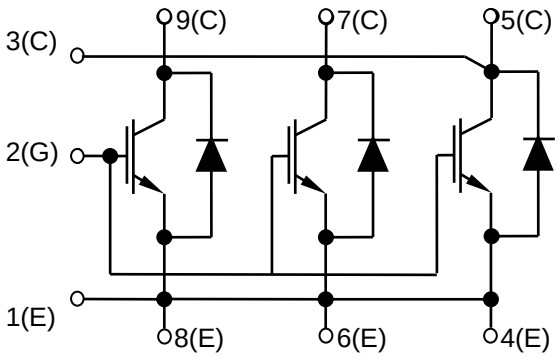


Fig. 1 Circuit configuration

Outline type code: A

(See Fig. 11 for further information)

Fig. 2 Package

ABSOLUTE MAXIMUM RATINGS

Stresses above those listed under 'Absolute Maximum Ratings' may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed. Exposure to Absolute Maximum Ratings may affect device reliability.

T_{case} = 25°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
V_{CES}	Collector-emitter voltage	V_{GE} = 0V, T_j = 125°C	6500	V
		V_{GE} = 0V, T_j = 25°C	6500	V
		V_{GE} = 0V, T_j = -40°C	6000	V
V_{GES}	Gate-emitter voltage		±20	V
I_C	Continuous collector current	T_{case} = 100°C	750	A
$I_{C(PK)}$	Peak collector current	1ms, T_{case} = 115°C	1500	A
P_{max}	Max. transistor power dissipation	T_{case} = 25°C, T_j = 125°C	11.1	kW
I^2t	Diode I^2t value	V_R = 0, t_p = 10ms, T_j = 125°C	470	kA^2s
V_{isol}	Isolation voltage – per module	Commoned terminals to base plate. AC RMS, 1 min, 50Hz	10.2	kV
Q_{PD}	Partial discharge – per module	IEC1287, V_1 = 6900V, V_2 = 5100V, 50Hz RMS	10	pC

THERMAL AND MECHANICAL RATINGS

Internal insulation material: AlN

Baseplate material: AlSiC

Creepage distance: 56mm

Clearance: 26mm

CTI (Comparative Tracking Index): >600

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
$R_{th(j-c)}$	Thermal resistance – transistor	Continuous dissipation – junction to case			9	°C/kW
$R_{th(j-c)}$	Thermal resistance – diode	Continuous dissipation – junction to case			18	°C/kW
$R_{th(c-h)}$	Thermal resistance – case to heatsink	Mounting torque 5Nm (with mounting grease)			6	°C/kW
T_j	Junction temperature	Transistor			125	°C
		Diode			125	°C
T_{stg}	Storage temperature range		-40		125	°C
	Screw torque	Mounting – M6			5	Nm
		Electrical connections – M4			2	Nm
		Electrical connections – M8			10	Nm

ELECTRICAL CHARACTERISTICS

T_{case} = 25°C unless stated otherwise.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
I_{CES}	Collector cut-off current	V_{GE} = 0V, V_{CE} = V_{CES}			4	mA
		V_{GE} = 0V, V_{CE} = V_{CES}, T_{case} = 125°C			90	mA
I_{GES}	Gate leakage current	V_{GE} = ± 20V, V_{CE} = 0V			1	µA
$V_{GE(TH)}$	Gate threshold voltage	I_C = 120mA, V_{GE} = V_{CE}	5.5	6.5	7.5	V
$V_{CE(sat)}$ †	Collector-emitter saturation voltage	V_{GE} = 15V, I_C = 750A		2.5		V
		V_{GE} = 15V, I_C = 750A, T_j = 125°C		3.4		V
I_F	Diode forward current	DC			750	A
I_{FM}	Diode maximum forward current	t_p = 1ms			1500	A
V_F †	Diode forward voltage	I_F = 750A		3.3		V
		I_F = 750A, T_j = 125°C		3.7		V
C_{ies}	Input capacitance	V_{CE} = 25V, V_{GE} = 0V, f = 1MHz		120		nF
Q_g	Gate charge	±15V		10		µC
C_{res}	Reverse transfer capacitance	V_{CE} = 25V, V_{GE} = 0V, f = 1MHz		2.3		nF
L_M	Module inductance			10		nH
R_{INT}	Internal resistance			90		µΩ
SC_{Data}	Short circuit current, I_{SC}	T_j = 125°C, V_{CC} = 4400V t_p ≤ 10µs, V_{GE} ≤ 15V $V_{CE\ (max)}$ = V_{CES} – L* x dI/dt IEC 60747-9		3700		A

Note:
† Measured at the auxiliary terminals
* L is the circuit inductance + L_M

ELECTRICAL CHARACTERISTICS

T_{case} = 25°C unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
$t_{d(off)}$	Turn-off delay time	I_C = 750A V_{GE} = ±15V V_{CE} = 3600V $R_{G(ON)}$ = 1.5Ω $R_{G(OFF)}$ = 6.8Ω C_{ge} = 330nF L_S ~ 200nH		4.8		µs
t_f	Fall time			720		ns
E_{OFF}	Turn-off energy loss			8600		mJ
$t_{d(on)}$	Turn-on delay time			620		ns
t_r	Rise time			340		ns
E_{ON}	Turn-on energy loss			5850		mJ
Q_{rr}	Diode reverse recovery charge	**Diode arm** I_F = 750A V_{CE} = 3600V dI_F/dt = 4000A/µs		1500		µC
I_{rr}	Diode reverse recovery current			1550		A
E_{rec}	Diode reverse recovery energy			2700		mJ

T_{case} = 125°C unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
$t_{d(off)}$	Turn-off delay time	I_C = 750A V_{GE} = ±15V V_{CE} = 3600V $R_{G(ON)}$ = 1.5Ω $R_{G(OFF)}$ = 6.8Ω C_{ge} = 330nF L_S ~ 200nH		4.8		µs
t_f	Fall time			800		ns
E_{OFF}	Turn-off energy loss			9100		mJ
$t_{d(on)}$	Turn-on delay time			550		ns
t_r	Rise time			300		ns
E_{ON}	Turn-on energy loss			7100		mJ
Q_{rr}	Diode reverse recovery charge	**Diode arm** I_F = 750A V_{CE} = 3600V dI_F/dt = 4200A/µs		2500		µC
I_{rr}	Diode reverse recovery current			2350		A
E_{rec}	Diode reverse recovery energy			4300		mJ

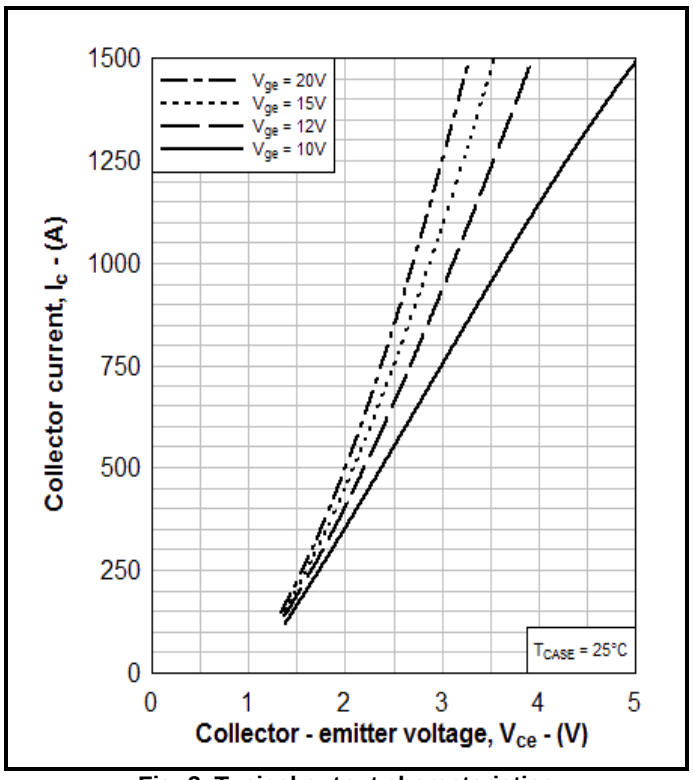


Fig. 3 Typical output characteristics

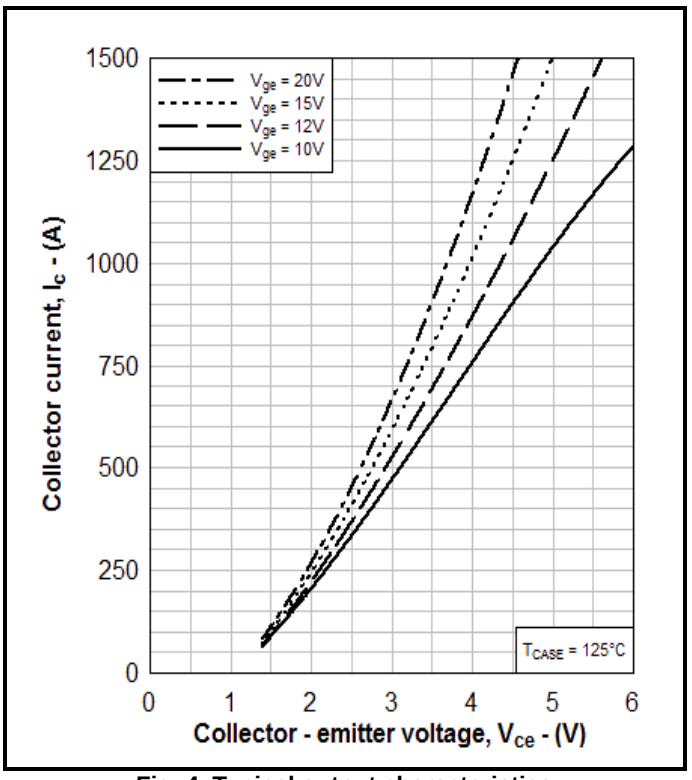


Fig. 4 Typical output characteristics

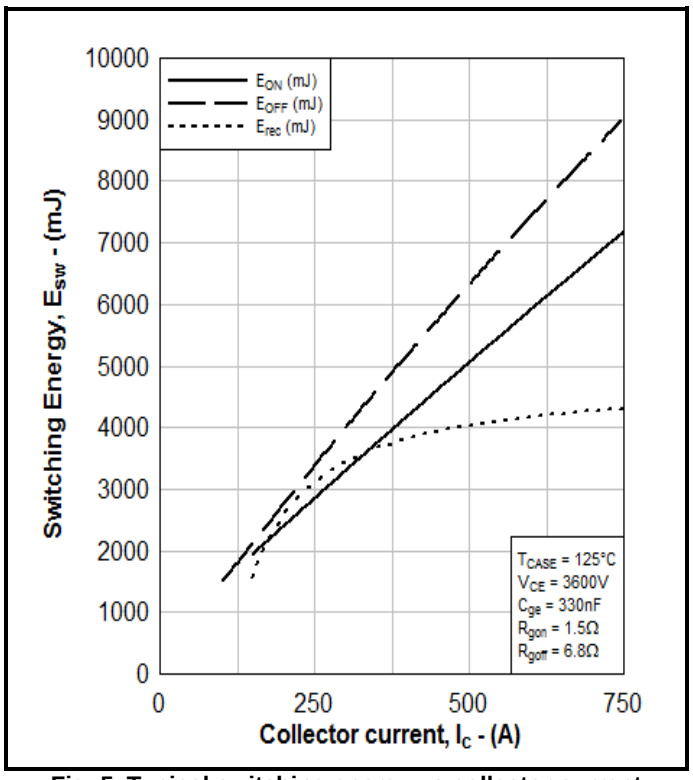


Fig. 5 Typical switching energy vs collector current

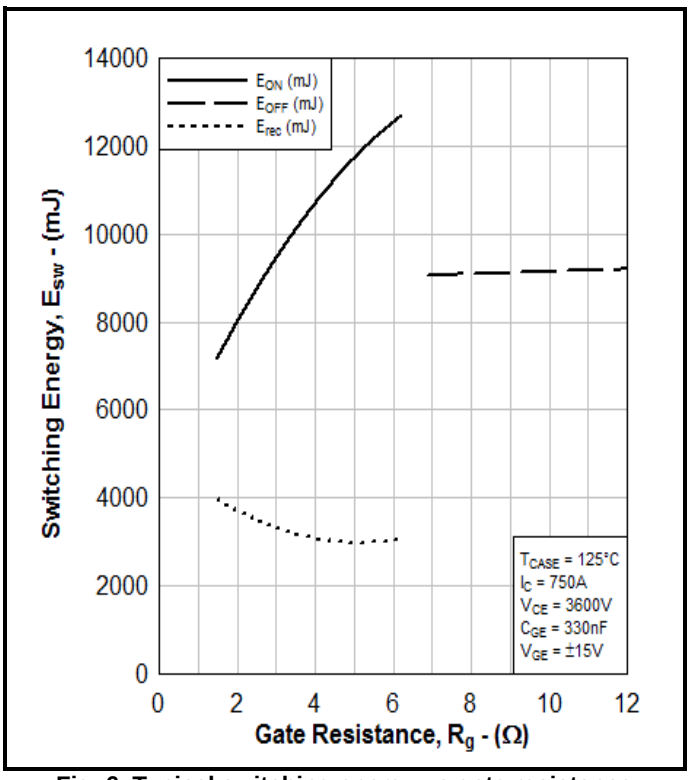


Fig. 6 Typical switching energy vs gate resistance

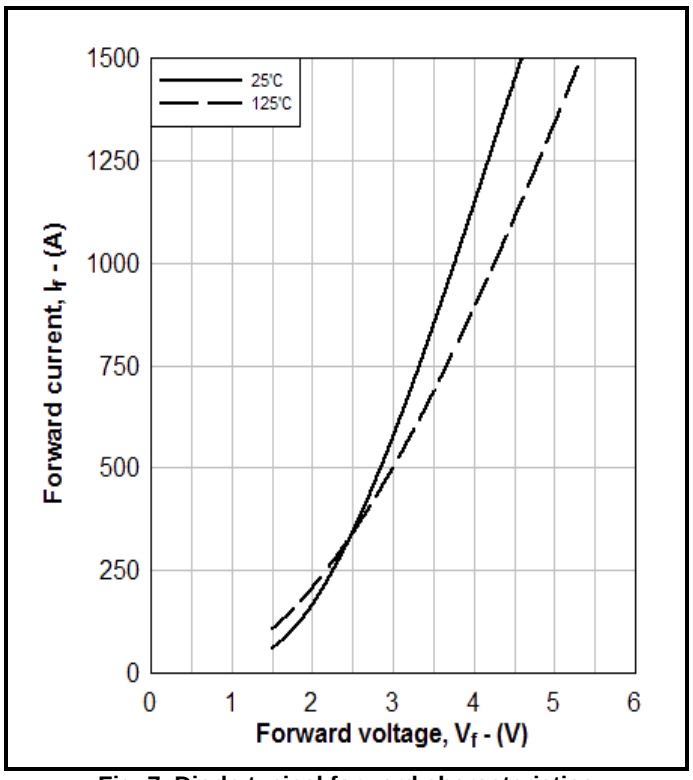


Fig. 7 Diode typical forward characteristics

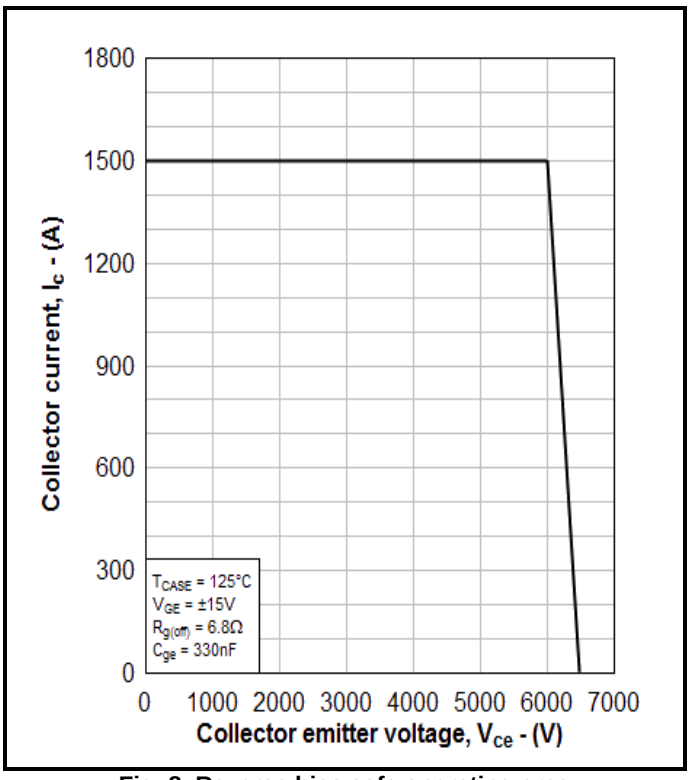


Fig. 8 Reverse bias safe operating area

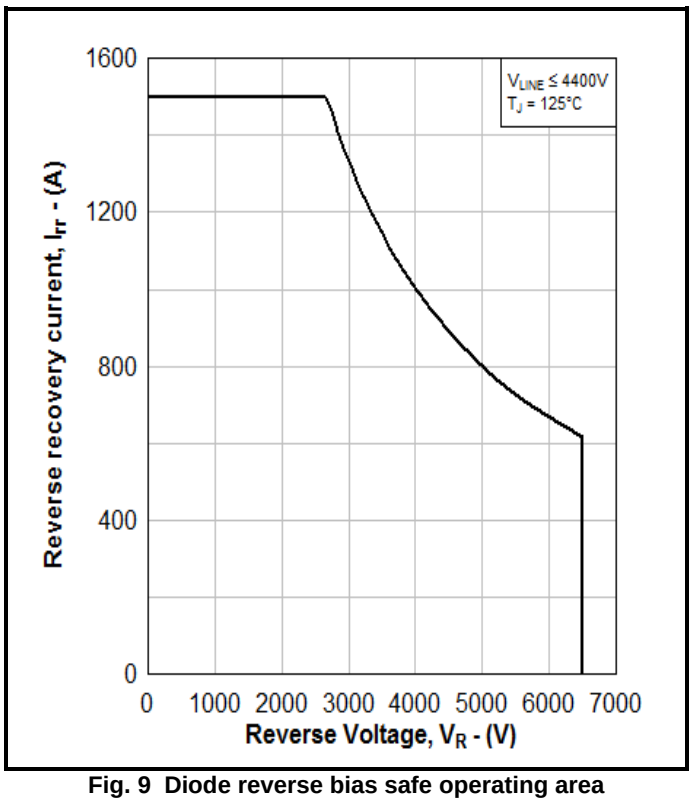


Fig. 9 Diode reverse bias safe operating area

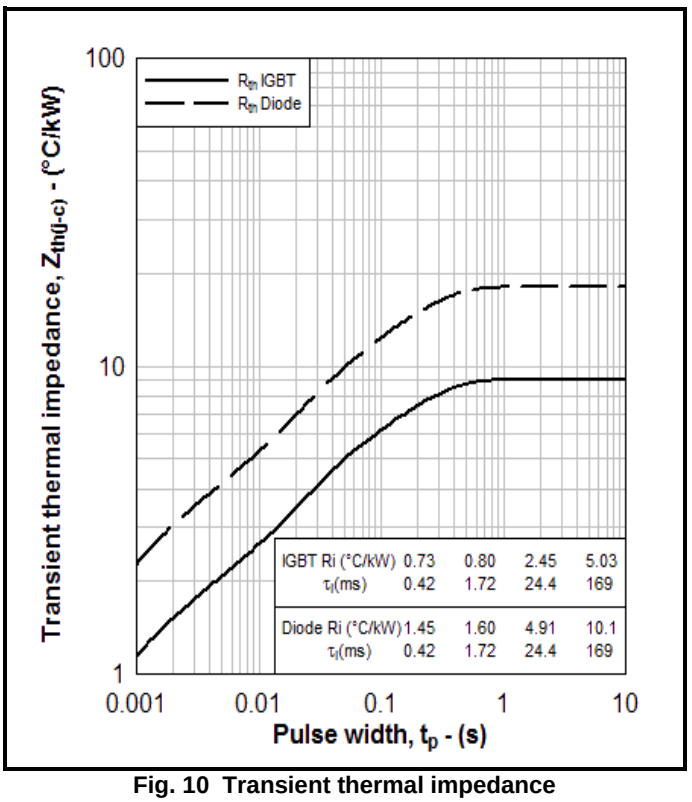
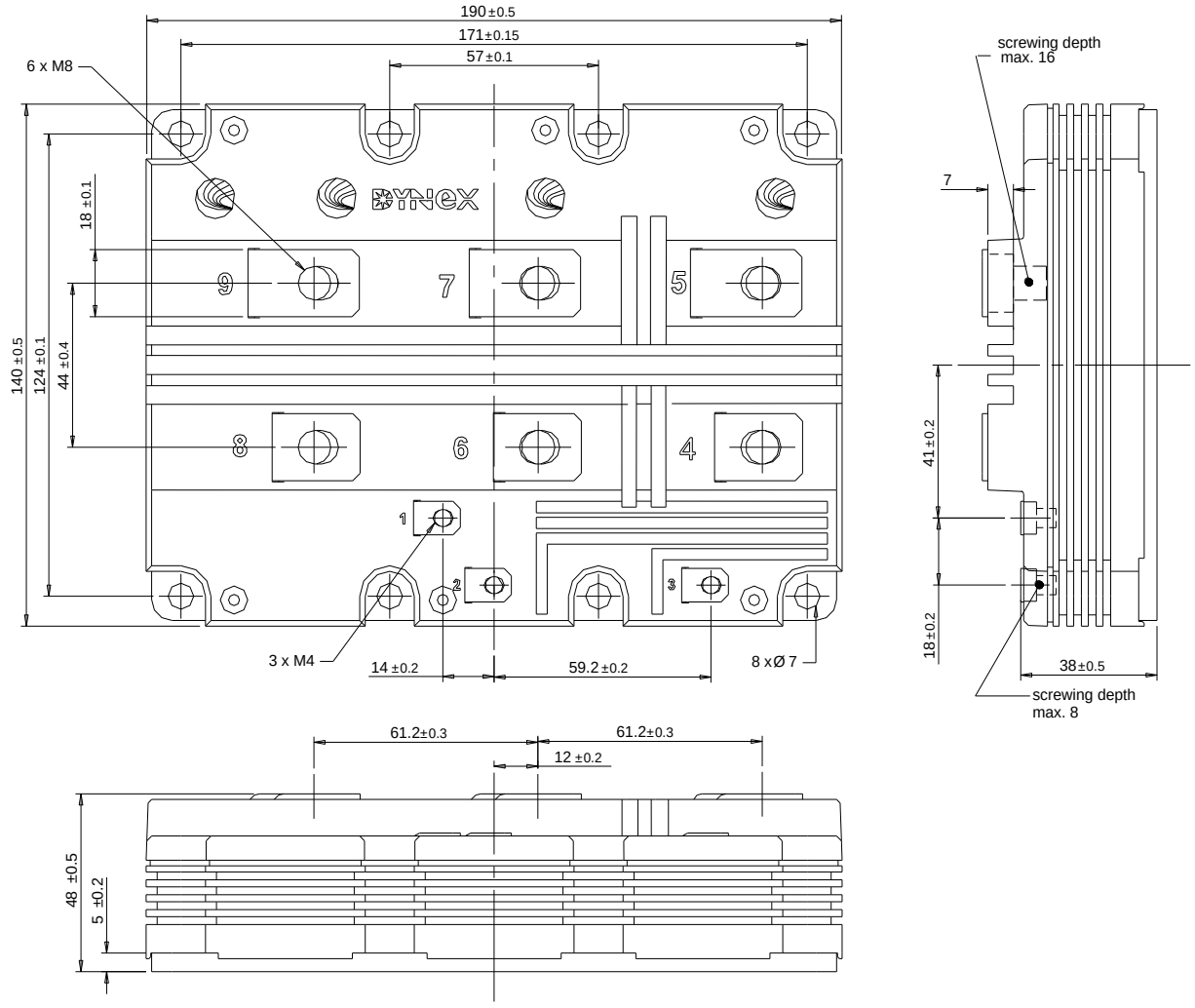


Fig. 10 Transient thermal impedance

PACKAGE DETAILS

For further package information, please visit our website or contact Customer Services.
All dimensions in mm, unless stated otherwise.
DO NOT SCALE.



Nominal Weight: 1700g

Module Outline Type Code: A

Fig. 11 Module outline drawing

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